



Cite this: DOI: 10.1039/d1nr90037d

## Correction: Suppression of metal-to-insulator transition using strong interfacial coupling at cubic and orthorhombic perovskite oxide heterointerfaces

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DOI: 10.1039/d1nr90037d  
rsc.li/nanoscale

Correction for 'Suppression of metal-to-insulator transition using strong interfacial coupling at cubic and orthorhombic perovskite oxide heterointerfaces' by Woonbae Sohn *et al.*, *Nanoscale*, 2021, **13**, 708–715, DOI: 10.1039/D0NR07545K.

The authors regret that in the original manuscript two co-authors, Kyeongpung Lee and Seungwu Han, were accidentally omitted from the authorship list. The correct authorship list is as displayed herein.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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## Supplementary Information

### **Suppression of metal to insulator transition using strong interfacial coupling at cubic and orthorhombic perovskite oxide heterointerface**

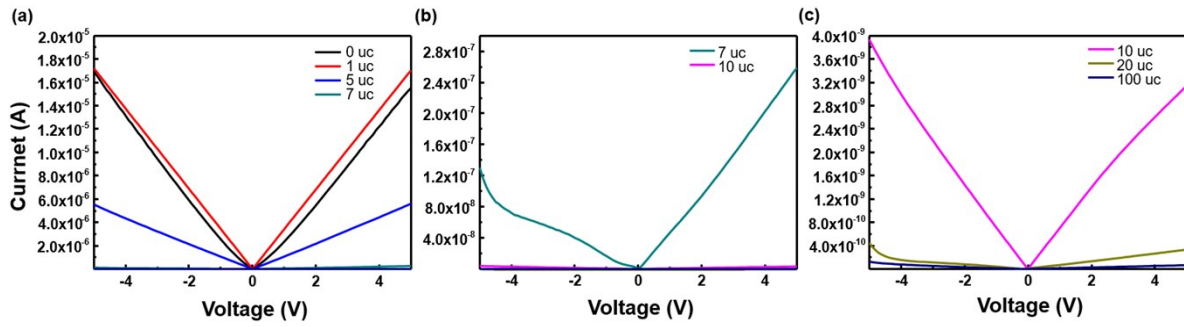
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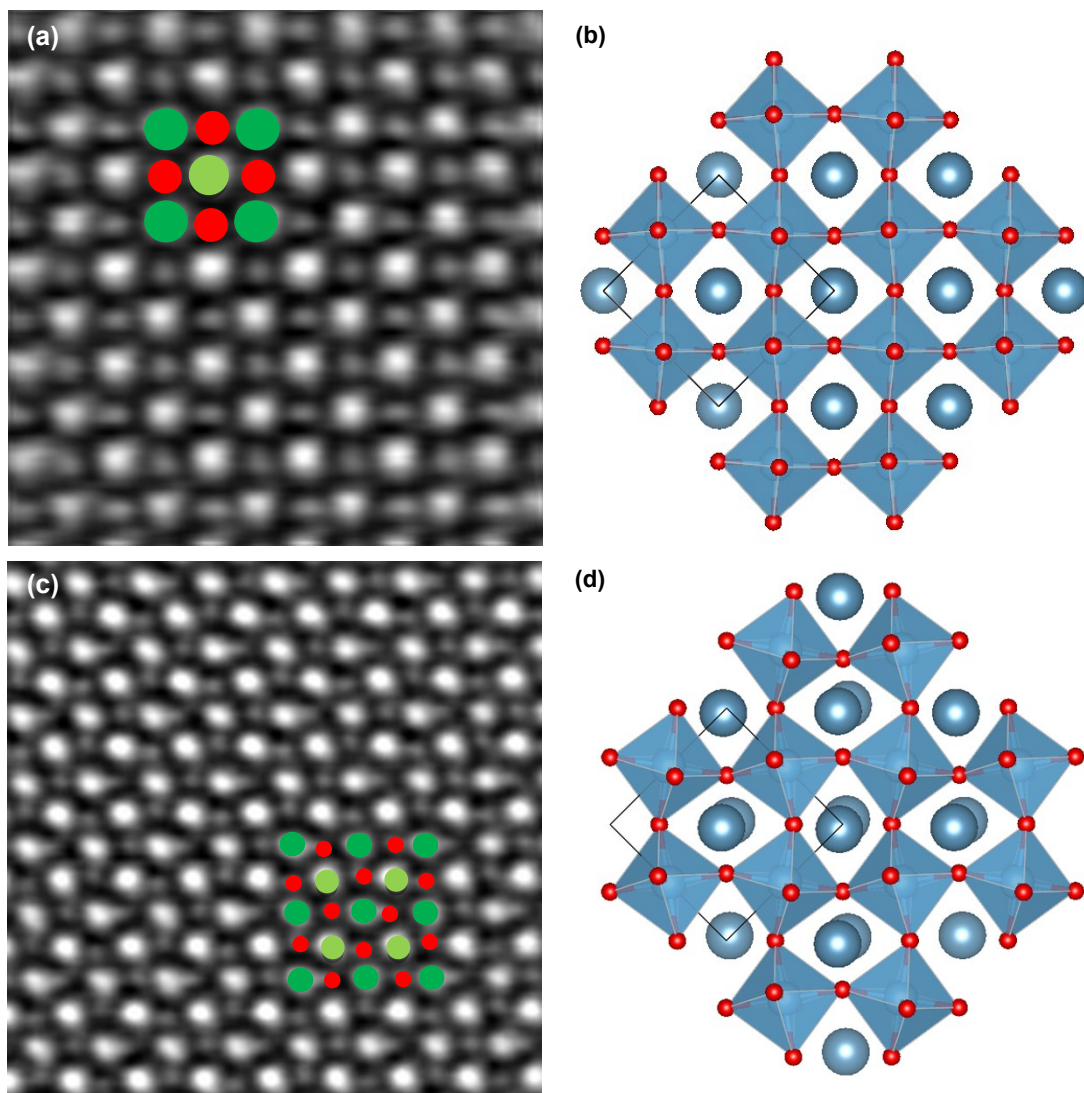
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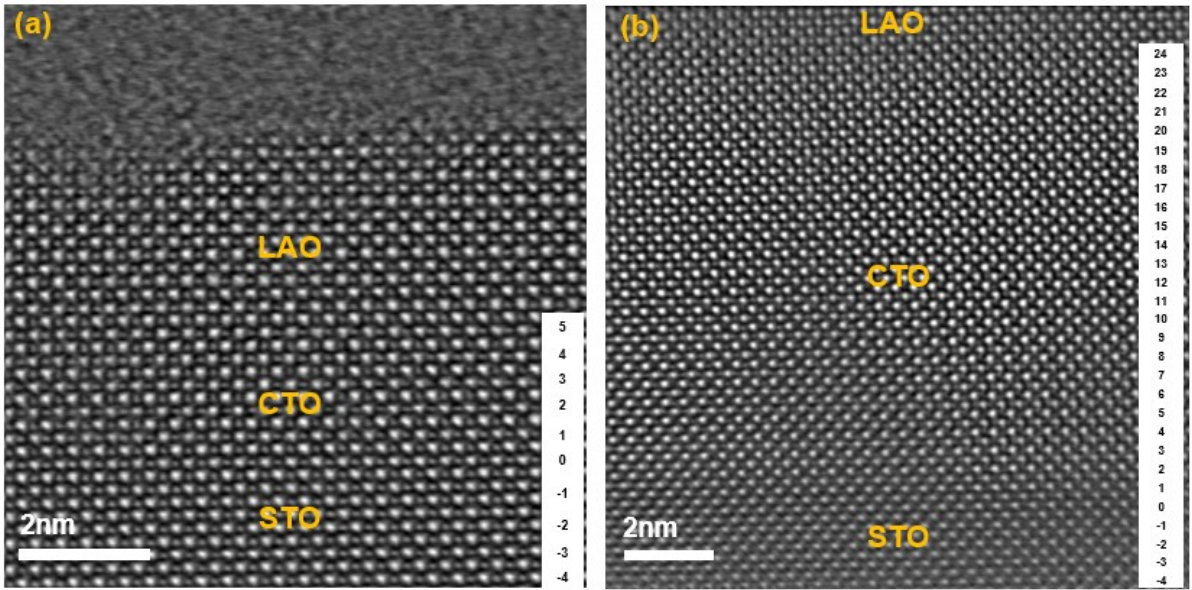
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**Fig. S1.** I-V curves of the LAO/CTO/STO heterostructures with different CTO interlayer thicknesses: (a) 0 - 7 uc, (b) 7 and 10 uc, (c) 10 - 100 uc.



**Fig. S2.** (a) Magnified iDPC STEM image of the 5 uc CTO film in the zone axis of  $[100]_p$  with marked atom position. (b) Atomic model of 5 uc CTO film, showing near-cubic symmetry. (c) Magnified iDPC STEM image of the 24 uc CTO film in the zone axis of  $[100]_p$  with marked atom position. (d) Atomic model of 24 uc CTO film, showing orthorhombic symmetry.



**Fig. S3.** iDPC STEM image of the (a) LAO/CTO (5 uc)/STO and (b) LAO/CTO (24 uc)/STO heterostructure with atomic row position at which Ti-O-Ti bonding angles are measured.